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On the Role of the N–N$^+$ Junction Doping Profile of a PIN Diode on Its Turn-Off Transient Behavior

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Abstract—This paper focuses on the role of the N–N$^+$ junction doping profile model of a PIN diode on its turn-off transient and, particularly, the influence of multiple epitaxies in the N–N$^+$ profile. A conventional doping profile model has been used in a previous work and an identification procedure for the main design parameters has been demonstrated. However the validity range of identified PIN-diode models appeared quite limited for hard current and voltage conditions. Readers have asked for the effect of a more advanced doping profile. The turn-off transient of an STTB506D device is considered from experimental and simulation point-of-view inside a fully characterized switching cell. A limitation of the conventional doping profile model is demonstrated and explained physically in order to introduce the necessity of a more complex doping profile. An advanced doping profile is then considered and a comparative study between experimental and simulated turn-off transient behavior of the device is established.

Index Terms—PIN diode.

I. INTRODUCTION

ACURATE modeling of the switching behavior of ultra-fast power diodes is very important for integrated power converter design, as the transient operations can lead to large voltage and current overshoots, power switching losses, and electromagnetic compatibility (EMC) contributions. Simulation relies on component models and associated parameters. In a previous study [1], it was shown that it is possible to extract good values of the main design parameters of a PiN diode: the doping concentration N$_D$ of the low-doped base region, the effective area A, the width $W_D$ of the low-doped base region, and the ambipolar lifetime $\tau$ in the low-doped base region of the PiN diode. This parameter extraction technique is applied to different devices under test.

The diode model with identified parameters [1] yields a very good accuracy between simulation and experimental results for medium current and voltage conditions, as shown in Fig. 1. However for higher current and voltage conditions, the diode model in [1] leads to waveforms that do not match experimental results. Readers have suggested that the diode model was too simple. So the current paper analyzes the cause of the discrepancies between simulation and experience to produce a better PiN diode model. It is considered a modified doping profile in

II. CIRCUIT MODEL OF THE SWITCHING CELL

A simple MOSFET transistor/power PiN diode is considered to exhibit turn-off behavior of the diode. The experimental and simulated circuits of the switching cell are pictured in

Fig. 1. Comparison of experimental and simulation results at various temperatures during turn-off transient of an STTA 81200 device ($I_F = 2 \ A, V_R = 160 \ V$) [1]. Voltage waveforms (top), current waveforms (bottom).
III. COMPARISON OF TWO DOPING PROFILE MODELS

For the design of the PiN diode doping profile, two cases are considered in 1-D: a simple epitaxial doping profile (conventional doping profile model) and a doping profile with a second epitaxy and the N₂ step, as in Fig. 3 (an advanced doping profile model [2]). Using the main design parameters estimated for the STTB506D diode in [1] and taking into account a conventional doping profile model, a good agreement was obtained between simulated and experimental waveforms of the voltage and current across the device for a forward current, \( I_F = 2 \, \text{A} \), for various values of the applied reverse voltage, \( V_R \) and for various operating temperatures (Fig. 1). The circuit in Fig. 2 is used for all simulations. The conventional doping profile model and the design parameter identification in [1] give a large and satisfactory validity range for the diode turn-off simulation.

However, this agreement between simulation and experiment is no longer valid when the voltage \( V_R \) is larger than 200 V, particularly at the end of the device turn-off transient, as for \( t > t_3 \), shown in Fig. 4. It may be noted that the simulated voltage waveform across the STTB506D diode presents a non-usual peak at instant \( t_4 \) (for the conventional doping profile model). Fig. 4 shows also that the advanced doping profile model produces a much better estimation of the current and voltage waveforms during the diode turn-off transient. The same design parameter identification procedure is used as for the conventional doping profile model.

The disagreement with the conventional doping profile model is due to the PiN-diode hard-switching during the turn-off transient. Indeed, the FEM simulation of the semiconductor device equations in the low-doped base region of the PiN-diode no longer presents a high concentration of holes to insure conduction (at \( t_3 < t < t_4 \) in Fig. 5). This phenomenon is analogous to the so-called Kirk effect in the power bipolar transistor. The current continuity has to be satisfied despite the local lack in charge carriers. Therefore, the electric field increases locally around the N–N⁺ junction to insure the current continuity (zoom in Fig. 6).

The electric field corresponds to an additional over-voltage \( V_{GE} \), as shown in Fig. 4. The simulated concentration of electrons in this region becomes higher than the doping profile to insure conduction by electron drift. This phenomenon explains the non-usual peak in the voltage waveform. So the FEM simulation shows clearly that to avoid this phenomenon, the doping level close to the N–N⁺ junction has to be higher in this particular region. Consequently, to obtain a soft-switching PiN diode during the turn-off transient, a doping profile with at least one step (N₂) is retained.
The advanced doping profile consists of a low-doped base region, of concentration $N_D$, to hold up a high reverse voltage and a thinner region, of concentration $N_2$ slightly larger than $N_D$. The $N_2$ region doping has to be high enough to insure the electron drift, as explained above, but not too much to enable conductivity modulation with high-level injection operating conditions. Using the main design parameters estimated for the STTB506D and taking into account the advanced doping profile model, the current and voltage waveforms across the STTB506D diode during its turn-off transient are simulated and given in Fig. 4 for the parameter set: $W_N = 15 \mu m$, $N_2 = 1.10^{15} \text{ cm}^{-3}$. The $N_2$ region width, $W_N$ and its doping concentration, $N_2$, are defined in Fig. 3. When the advanced doping profile model is considered instead of the conventional...
one for the PiN diode, the peak in the simulated voltage waveform across the diode under test does not appear and a good agreement between simulated and experimental voltage and current waveforms is found, as shown in Fig. 4.

A systematic assessment of the validity range of the advanced diode model is to be carried out. This systematic comparison between simulations and measurements should help ascertain if the obtained values of \( W_N \) and \( N_2 \) are the best practical values for the STTB056D device. If the validity range is not satisfactory, it is then interesting to question if other epitaxial steps have to be considered at the N–N\(^+\) junction of the PiN diode. So far, the authors have shown that the proposed advanced doping profile model brings a significant improvement in accuracy in the case of the PiN diode turn-off simulation and for hard voltage and current conditions. They have successfully applied the advanced doping profile model to various commercial devices.

IV. CONCLUSION

In a previous work, the authors demonstrated the usefulness of a simple 1-D doping profile for the simulation of the PiN diode transients. The identification of the main design parameters was proposed and a large validity range obtained for the identified models. However a disagreement between simulation and experiment appears in the case of hard operating conditions. This letter has shown the effect of the conventional doping profile model on the simulation of turn-off in these conditions. It is necessary to consider an advanced doping profile for the PiN diode (such as the N–N\(^+\) step profile) to obtain better simulation results in hard switching conditions. The simulation results then agree satisfactorily with experimental results. Some improvements are also noted with the automation of the identification procedure of the WN and N2 parameters.

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